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Kind regards,

Team Nexperia

PMF87EN

30 V, single N-channel Trench MOSFET

1 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a SOT323 (SC-70) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

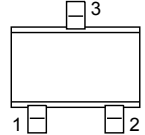
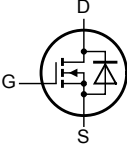
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	1.9	A
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 1.7\text{ A}; T_j = 25\text{ °C}$	-	67	80	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SC-70 (SOT323)</p>	 <p>017aaa253</p>
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMF87EN	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes

Type number	Marking code
PMF87EN	VA% [1]

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	30	V	
V_{GS}	gate-source voltage		-20	20	V	
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	1.9	A
		$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	1.7	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	1.1	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	6.8	A	
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	275	mW
			[1]	-	355	mW
		$T_{sp} = 25\text{ °C}$		-	1810	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _s	source current	T _{amb} = 25 °C	[1]	-	0.7	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

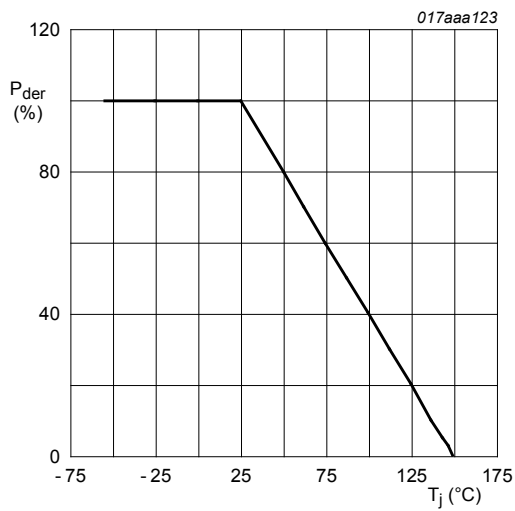


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

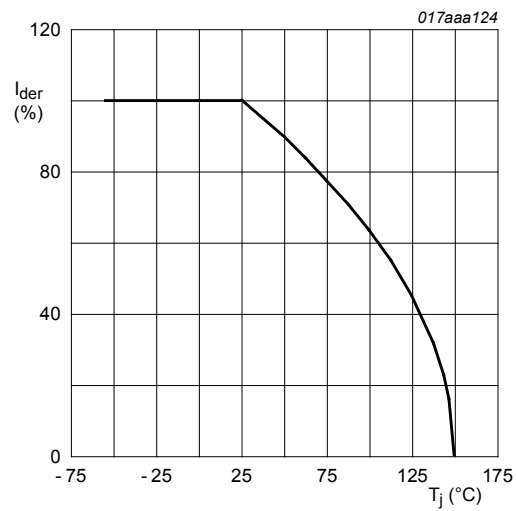
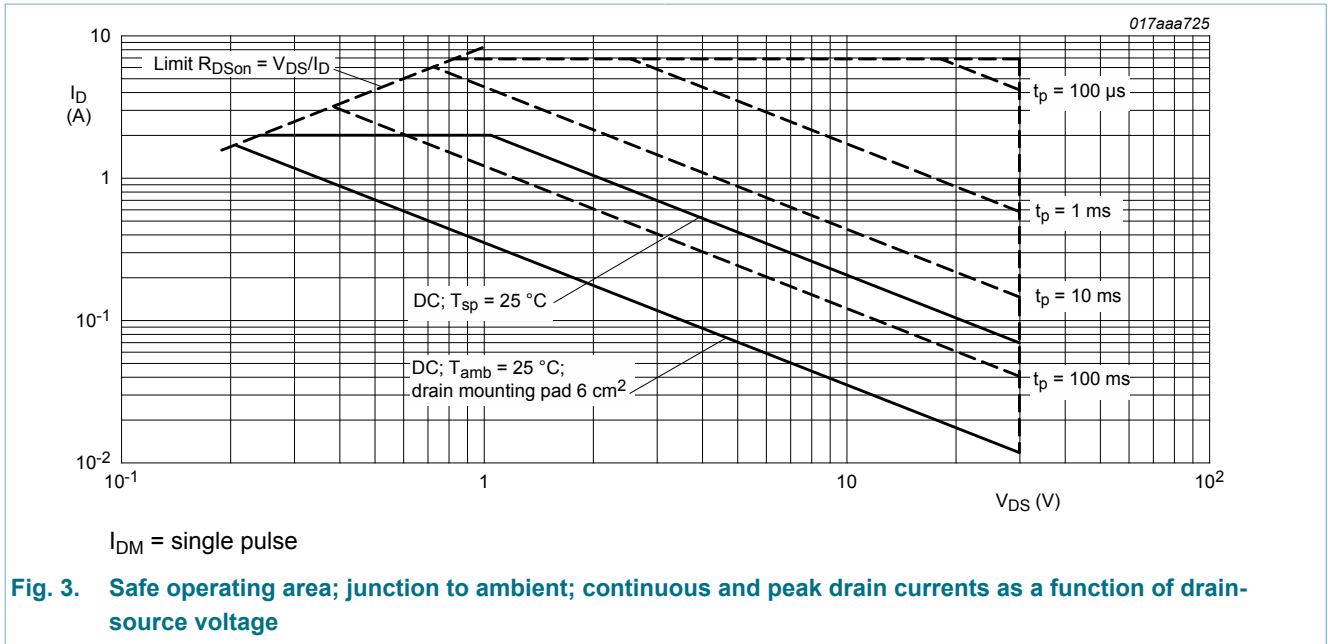


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



6. Thermal characteristics

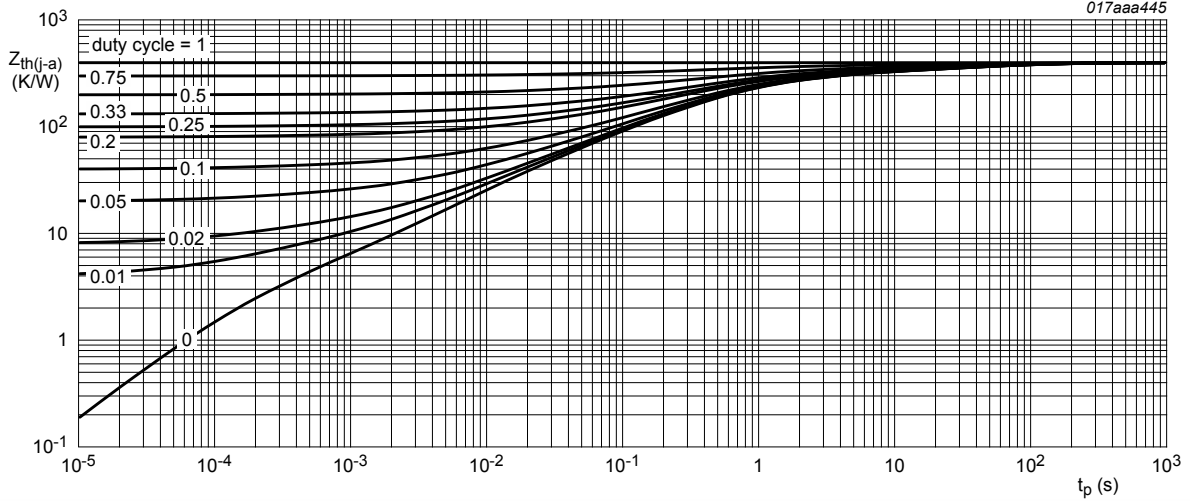
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	394	453	K/W
			[2]	-	308	354	K/W
			[3]	-	263	302	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	60	70	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

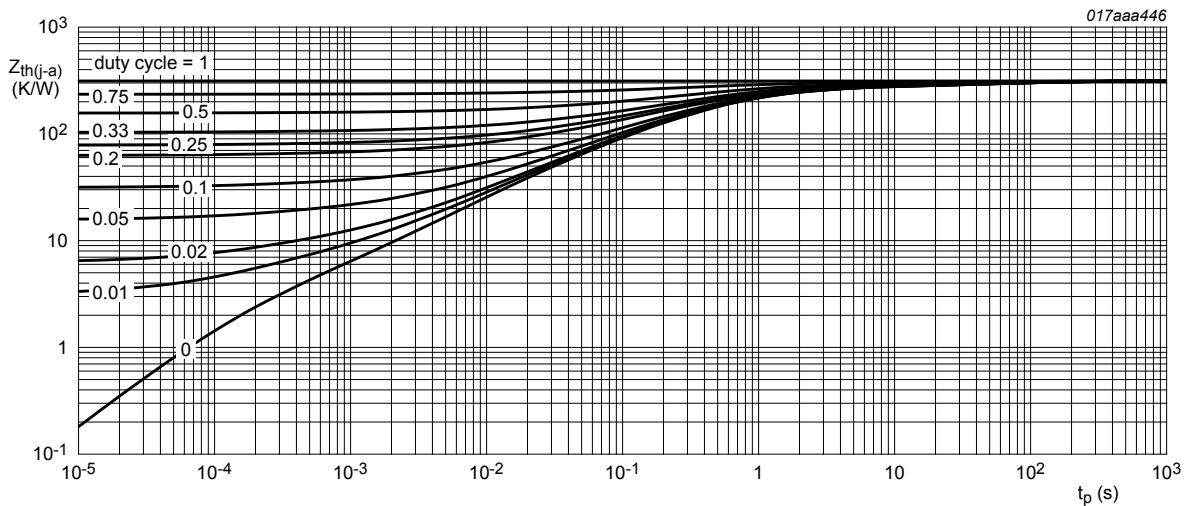
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 , $t \leq 5\text{ s}$.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1	1.5	2.5	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	10	μA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 1.7 A; T _j = 25 °C	-	67	80	mΩ
		V _{GS} = 10 V; I _D = 1.7 A; T _j = 150 °C	-	101	120	mΩ
		V _{GS} = 4.5 V; I _D = 1.4 A; T _j = 25 °C	-	87	110	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 1.7 A; T _j = 25 °C	-	5.8	-	S
Dynamic characteristics						
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 1.7 A; V _{GS} = 10 V; T _j = 25 °C	-	3.1	4.7	nC
Q _{GS}	gate-source charge		-	0.46	-	nC
Q _{GD}	gate-drain charge		-	0.42	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C	-	135	-	pF
C _{oss}	output capacitance		-	33	-	pF
C _{rss}	reverse transfer capacitance		-	14	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 1.7 A; V _{GS} = 10 V; R _{G(ext)} = 6 Ω; T _j = 25 °C	-	3	-	ns
t _r	rise time		-	14	-	ns
t _{d(off)}	turn-off delay time		-	15	-	ns
t _f	fall time		-	6	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 0.7 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V

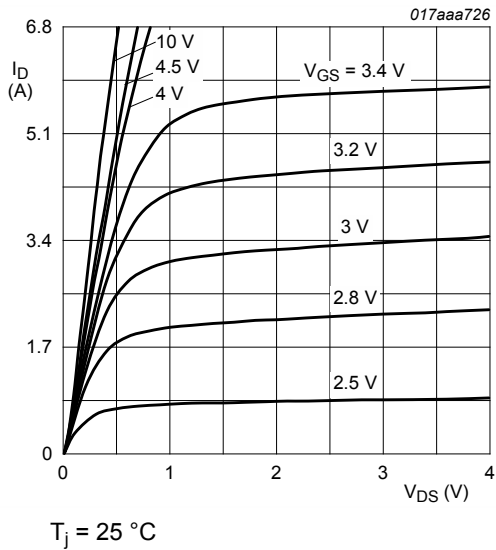


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

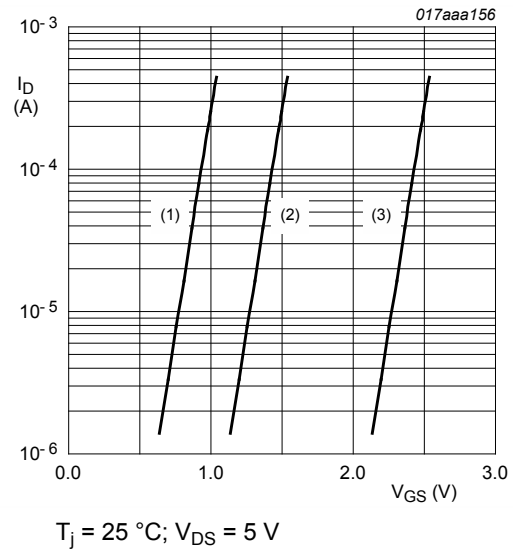


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

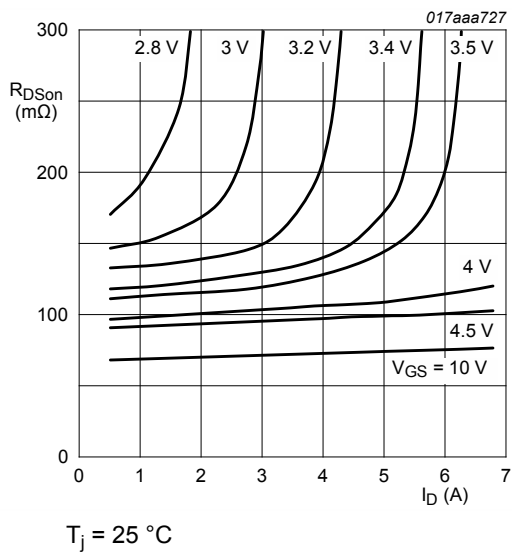


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

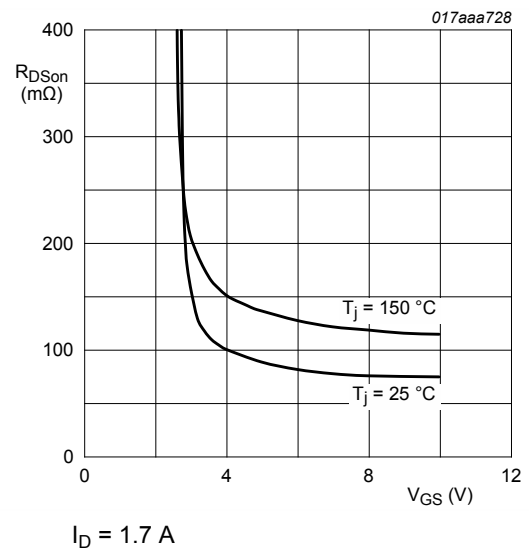
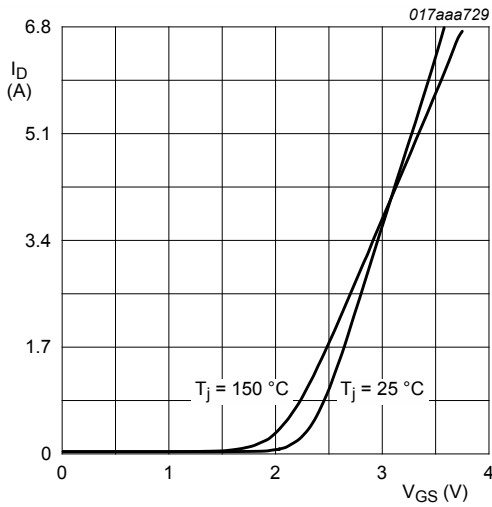


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

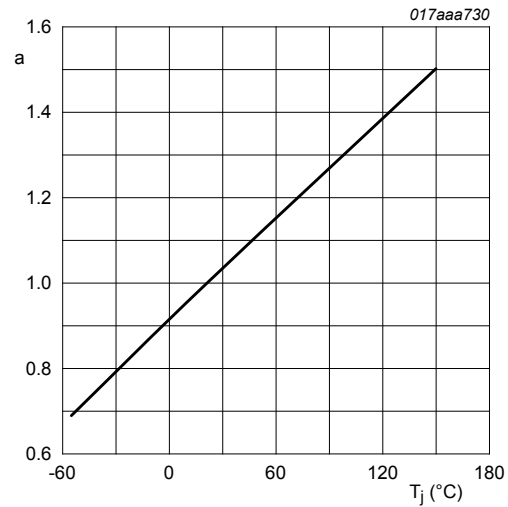
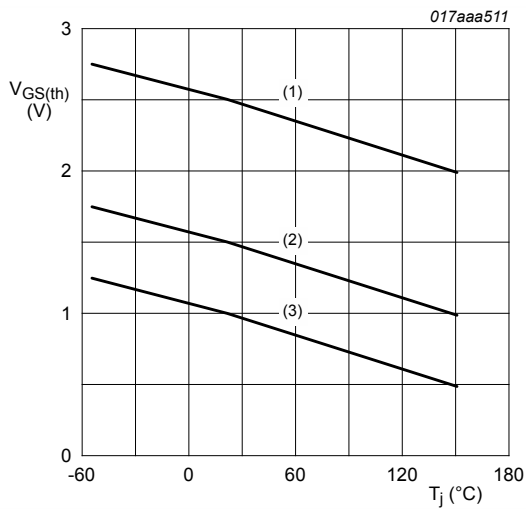


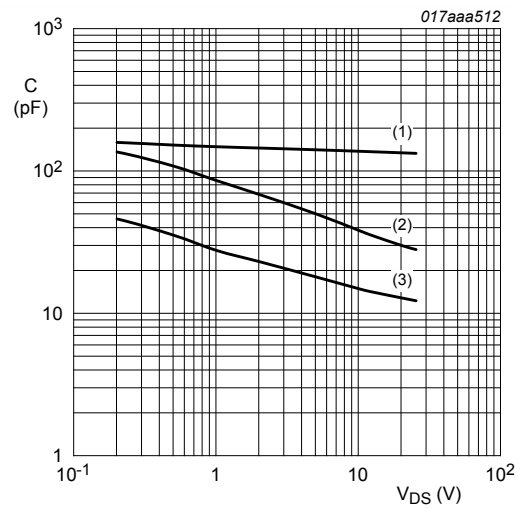
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



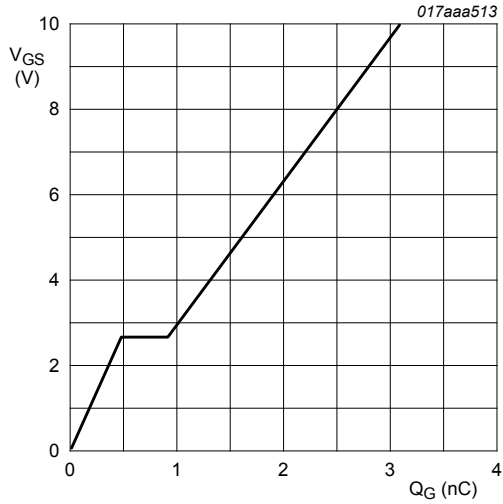
$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$
 (1) maximum values
 (2) typical values
 (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$
 (1) C_{iss}
 (2) C_{oss}
 (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 2\text{ A}$; $V_{DS} = 15\text{ V}$; $T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

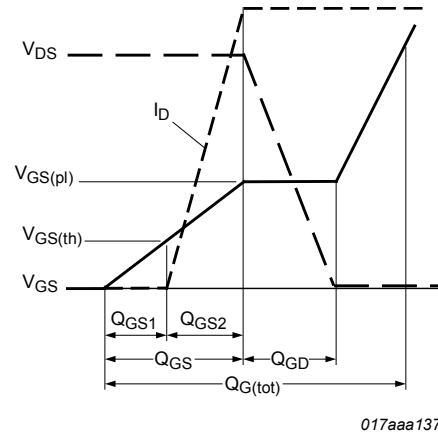
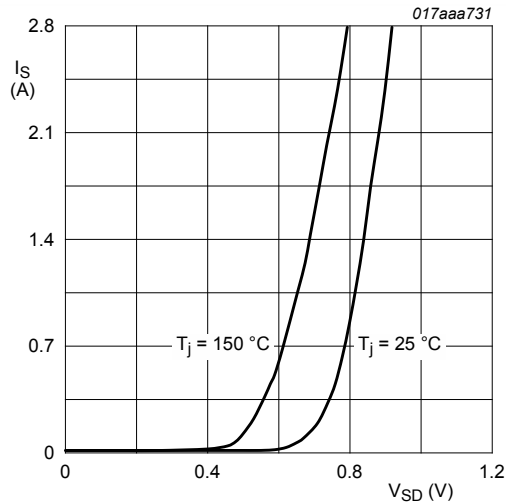


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

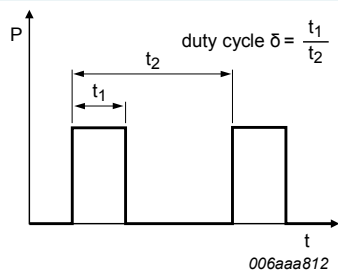


Fig. 17. Duty cycle definition

9. Package outline

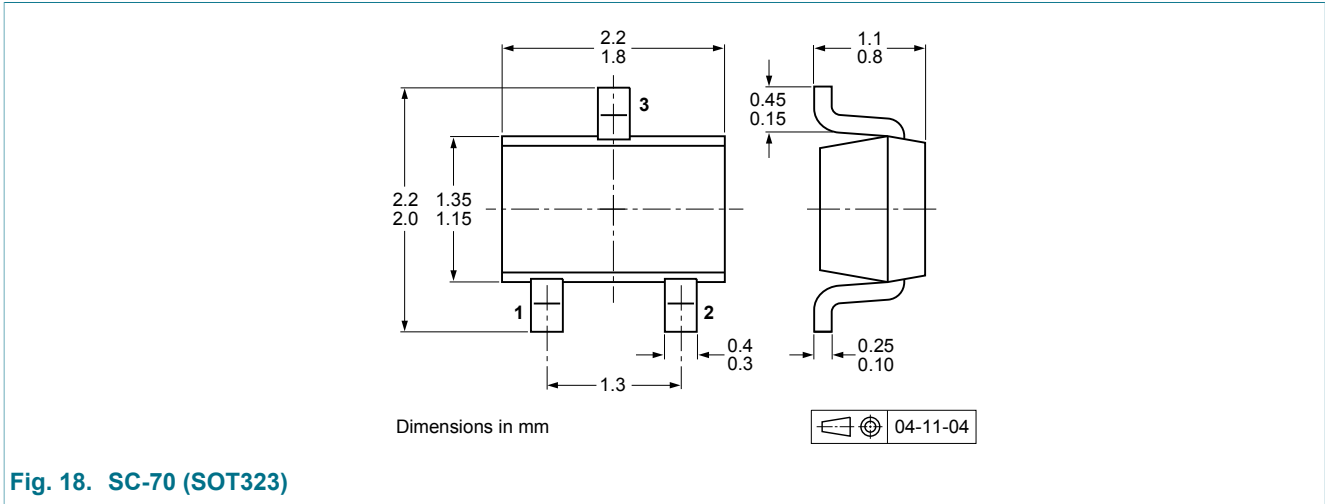


Fig. 18. SC-70 (SOT323)

10. Soldering

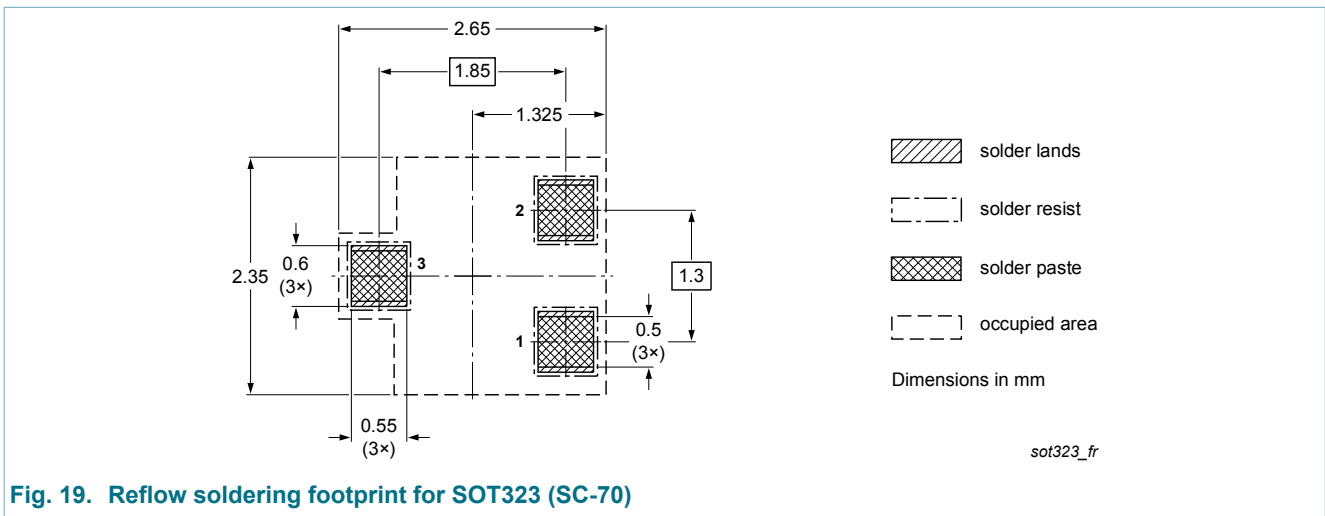


Fig. 19. Reflow soldering footprint for SOT323 (SC-70)

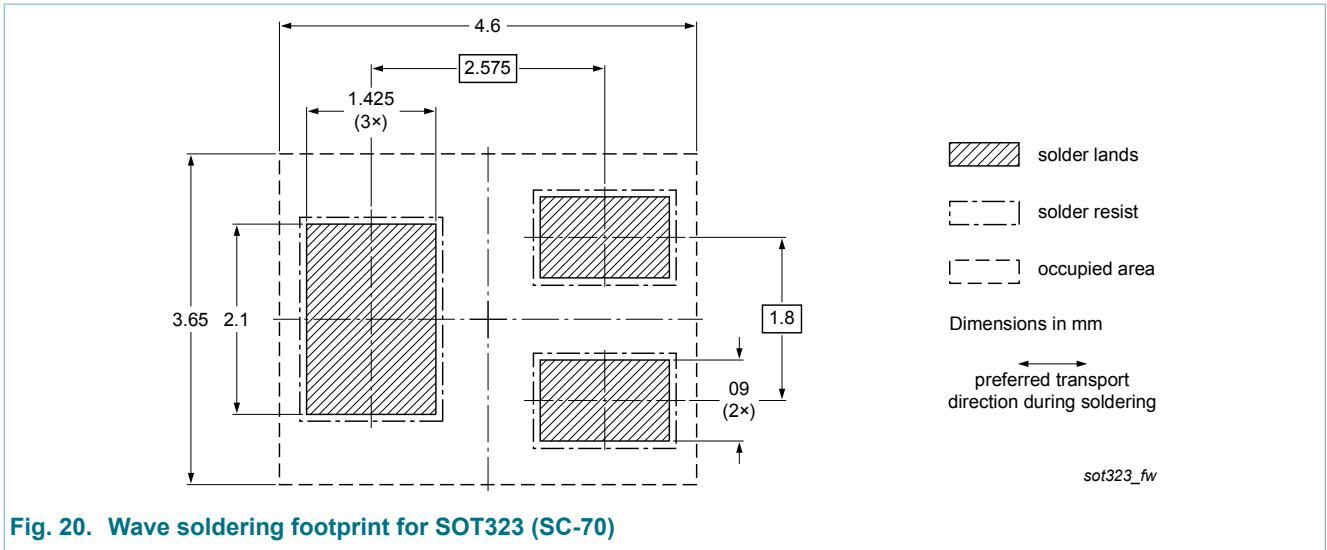


Fig. 20. Wave soldering footprint for SOT323 (SC-70)

11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF87EN v.1	20120801	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	4
7	Characteristics	5
8	Test information	9
9	Package outline	10
10	Soldering	10
11	Revision history	11
12	Legal information	12
12.1	Data sheet status	12
12.2	Definitions	12
12.3	Disclaimers	12
12.4	Trademarks	13

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